

Low Power Precision Operational Amplifier

PM1012

FEATURES

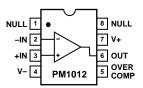
Low Supply Current: 600 μA Max Very Low Offset: 35 μV Max Low Drift: 1.5 μV/°C Max Very Low Bias Current 25°C: 100 pA Max

Low Noise: 0.5 μV p-p Typ

High Common-Mode Rejection: 114 dB Min

PIN CONNECTIONS

Plastic Mini-DIP (P Suffix) 8-Lead SO (S Suffix)



GENERAL DESCRIPTION

The PM1012 is a general purpose, precision operational amplifier. Offering several performance enhancements over industry-standard precision op amps such as the OP07, the PM1012 requires less than 1/6 the supply current. These enhancements include exceptionally low bias currents of only ± 80 pA, typical, over the full military temperature range, and 132 dB of common-mode rejection and power-supply rejection. The PM1012's low offset voltage of 35 μV maximum frees the user from external nulling in most circuits.

An open-loop gain of two million into a 10 k Ω load ensures that excellent linearity is maintained even in high gain configurations, and 5 mA of output current allows 2 k Ω loads to be driven with an open-loop gain of one million. The PM1012 offers low noise, especially for a low power amplifier—only $17 \text{ nV/} \overline{\text{Hz}}$ at 10 Hz. Exceptionally low current noise minimizes

noise contributions when high source impedances are used. The PM1012 may be overcompensated, using Pin 5 to limit the amplifier's bandwidth, further reducing system noise and increasing stability with large capacitive loads.

The PM1012 conforms to the OP07 pinout with nulling through Pins 1 and 8 to the positive supply. It offers an upgrade to the OP07 in sockets where reduced power dissipation or low bias currents are attractive. It may also be used as an upgrade from the OP12, OP05 and 725 type op amps. The PM1012 may replace 741 type op amps by removing the nulling potentiometer, if used.

PM1012-SPECIFICATIONS

ELECTRICAL CHARACTERISTICS (@ $V_S = \pm 15 \text{ V}$, $V_{CM} = 0 \text{ V}$, $T_A = +25 ^{\circ}\text{C}$, unless otherwise noted)

				PM1012G		
Parameter	Symbol	Conditions	Min	Тур	Max	Units
Input Offset Voltage	V _{OS}	(Note 1)		10	50	μV
				25	120	μV
Long-Term						
V _{OS} Stability	ΔV_{OS} /Time			0.3		μV/Month
Input Offset Current	I _{OS}	(Note 1)		20	150	pA
•				30	200	pA
Input Bias Current	I_B	(Note 1)		± 30	± 150	pA
				± 40	± 200	pA
Input Noise Voltage	e _n p-p	0.1 Hz to 10 Hz		0.5		μV p-p
Input Noise Voltage Density	$\mathbf{e}_{\mathbf{n}}$	$f_O = 10 \text{ Hz}^2$		17	30	nV/√ Hz
		$f_{\rm O} = 1000 \; Hz^3$		14	22	nV/√ Hz
Input Noise Current Density	In	$f_O = 10 \text{ Hz}$		20		fA/√Hz
Large-Signal Voltage Gain	A_{VO}	$V_{\rm O} = \pm 12 \text{ V}; R_{\rm L} = 10 \text{ k}\Omega$	200	2000		V/mV
		$V_O = \pm 10 \text{ V}; R_L = 2 \text{ k}\Omega$	120	1000		V/mV
Common-Mode Rejection	CMR	$V_{CM} = \pm 13.5 \text{ V}$	110	132		dB
Power-Supply Rejection	PSR	$V_S = \pm 2 \text{ V to } \pm 20 \text{ V}$	110	132		dB
Input Voltage Range	IVR	(Note 4)	±13.5	± 14.0		V
Output Voltage Swing	V_{O}	$R_L = 10 \text{ k}\Omega$	±13	± 14		V
Slew Rate	SR		0.1	0.2		V/μs
Full-Power Bandwidth	BW_P			3		kHz
Gain Bandwidth Product	GBW	$A_{V} = +100$		0.5		MHz
Supply Current	I_{SY}	(Note 1)		380	600	μA
Supply Voltage	$V_{\rm S}$	Operating Range	±2	±15	±20	V

Specifications subject to change without notice.

ELECTRICAL CHARACTERISTICS (@ $V_S = \pm 15 \text{ V}$, $V_{CM} = 0 \text{ V}$, $-40 ^{\circ}\text{C} \le T_A \le +85 ^{\circ}\text{C}$ for PM1012GP, GS, unless otherwise noted)

				PM1012G		
Parameter	Symbol	Conditions	Min	Тур	Max	Units
Input Offset Voltage	Vos			20	120	μV
	mar.	27		30	200	μV
Average Temperature	TCV _{OS}	(Note 1)		0.0	1 5	- JU/0C
Coefficient of V _{OS} Input Offset Current	T	(Note 1)		0.2 20	1.5 230	μV/°C
input Offset Current	I_{OS}	(Note 1)		40	300	pA pA
Average Temperature	TCIos			40	300	l pr
Coefficient of I _{OS}	10103			0.3	2.5	pA/°C
Input Bias Current	I_{B}	(Note 1)		± 35	± 230	pA
•				± 50	± 300	pА
Average Temperature						
Coefficient of I _B	TCI_B			0.3	2.5	pA/°C
Large Signal Voltage Gain	Avo	$V_O = \pm 12 \text{ V}; R_L = 10 \text{ k}\Omega$	150	1500		V/mV
	C) (D)	$V_{\rm O} = \pm 10 \text{ V}; R_{\rm L} = 2 \text{ k}\Omega$	100	800		V/mV
Common-Mode Rejection	CMR	$V_{CM} = \pm 13.5 \text{ V}$	108	130		dB
Power Supply Rejection	PSR	$V_S = \pm 2.5 \text{ V to } \pm 20 \text{ V}$	108	128		dB V
Input Voltage Range Output Voltage Swing	IVR	(Note 2) $R_L = 10 \text{ k}\Omega$	±13.5 ±13	$\pm 14.0 \\ \pm 14$		V
Slew Rate	V _O SR	ICL — 10 N22	0.05	0.15		V V/µs
Supply Current	I _{SY}	(Note 1)	0.03	400	800	μΑ
Supply Voltage	$V_{\rm S}$	Operating Range	±2.5	±15	±20	V V
Supply voltage	V S	Operating realige	± 2.5	-10	± ≈0	, v

NOTES

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¹These specifications apply for ± 2 V ≤ V_S ≤ ± 20 V and -13.5 V ≤ V_{CM} ≤ +13.5 V (for V_S = ± 15 V). ²10 Hz noise voltage density is sample tested. Devices 100% tested for noise are available on request.

³Sample tested.

⁴Guaranteed by CMR test.

 $^{^{1}} These \ specifications \ apply \ for \ \pm 2.5 \ V \leq V_{S} \leq \pm 20 \ V \ and \ -13.5 \ V \leq V_{CM} \leq +13.5 \ V \ (for \ V_{S} = \pm 15 \ V).$

²Guaranteed by CMR test.

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PM1012

ABSOLUTE MAXIMUM RATINGS1

Supply Voltage
Input Voltage ² ±20 V
Differential Input Voltage ³ ±1 V
Differential Input Current ³ ±10 mA
Output Short-Circuit Duration Indefinite
Operating Temperature Range
PM1012G (P, S)40°C to +85°C
Storage Temperature Range65°C to +150°C
Junction Temperature Range65°C to +150°C
Lead Temperature (Soldering, 60 sec) +300°C

Package Type	θ_{JA}^{4}	θ_{JC}	Units	
8-Lead Plastic DIP (P)	103	43	°C/W	
8-Lead SO (S)	158	43	°C/W	

NOTES

¹Absolute maximum ratings apply to both DICE and packaged parts, unless otherwise noted.

 $^2 For \ supply \ voltages \ less than \ \pm 20 \ V,$ the absolute maximum input voltage is equal to the supply voltage.

³The PM1012's inputs are protected by back-to-back diodes. Current-limiting resistors are not used in order to achieve low noise. Differential input voltages greater than 1 V will cause excessive current to flow through the input protection diodes unless limiting resistance is used.

 $^4\theta_{JA}$ is specified for worst case mounting conditions, i.e., θ_{JA} is specified for device in socket for cerdip, and P-DIP packages; θ_{JA} is specified for device soldered to printed circuit board for SO package.

ORDERING GUIDE

Model	Temperature	Package	Package
	Range	Description	Options
PM1012GP	-40°C to +85°C	Plastic DIP	N-8
PM1012GS	-40°C to +85°C	SOIC	SO-8

CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the PM1012 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

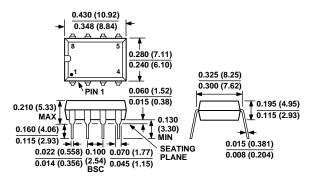


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OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

8-Lead Plastic DIP (N-8)



8-Lead SOIC (SO-8)

